any one of an opening part or a depressed part formed in an insulating film on a substrate;

a barrier layer covering said opening part or said depressed part, said barrier layer being made of a first material;

a metal growth promoting layer on said barrier layer, said metal growth promoting layer being made of a second material that is different from said first material of said barrier layer; and

an electroconductive layer embedded in said opening part or said depressed part via said barrier layer and said metal growth promoting layer.

3. (Amended Three Times) An embedded electroconductive layer comprising:

any one of an opening part or a depressed part formed in an insulating film on a substrate;

a barrier layer covering said opening part or said depressed part;

a metal growth promoting layer on said barrier layer, said metal growth promoting layer being made of a material different from that of said barrier layer; and

an electroconductive layer embedded in said opening part or said depressed part via said barrier layer and said metal growth promoting layer;

D2 cont'd. F2.

wherein said metal growth promoting layer is a TiN layer containing oxygen at a lower concentration than said barrier layer.

37. (New Claim) The embedded electroconductive layer according to claim 1, wherein said metal growth promoting layer has a thickness of at least approximately 10nm.

38. (New Claim) The embedded electroconductive layer according to claim 37, wherein said metal growth promoting layer has a thickness of approximately 20nm.

39. (New Claim) The embedded electroconductive layer according to claim 1, wherein said barrier layer has a thickness of at least approximately 10nm.

D3

40. (New Claim) The embedded electroconductive layer according to claim 3, wherein said first material is WN_x, where x is a variable such that $0 \leq x \leq 1$.

41. (New Claim) The embedded electroconductive layer according to claim 3, wherein said first material is TaN_x, where x is a variable such that $0 \leq x \leq 1$.